**Product data sheet** 

## 1. General description

Hyperfast power diode in 2-lead TO220F plastic package.



## 2. Features and benefits

- Soft reverse recovery
- Fast switching
- Isolated plastic package
- Low leakage current
- · Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT
- Package meets UL94V0 which guaranteed by epoxy mold compound

## 3. Applications

- · Active PFC in air conditioner
- · High frequency switched-mode power supplies
- Power Factor Correction (PFC)

## 4. Quick reference data

#### Table 1. Quick reference data

	Conditions	Notes		Values		Unit
maximum rating						
repetitive peak reverse voltage				650		V
average forward current	δ = 0.5 ; square-wave pulse; Fig. 1; Fig. 2		30			А
repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; square-wave pulse		60			А
non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3		250			Α
	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			275		А
Parameter	Conditions	Notes	Min	Тур	Max	Unit
aracteristics						
forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	1.85	2.50	V
	I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.45	2.10	V
characteristics						
reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/µs};$ $T_i = 25 \text{ °C}; Fig. 6$		-	23	-	ns
	repetitive peak reverse voltage average forward current repetitive peak forward current non-repetitive peak forward current Parameter aracteristics forward voltage	repetitive peak reverse voltage  average forward current $\delta = 0.5$ ; square-wave pulse; Fig. 1; Fig. 2  repetitive peak forward current $\delta = 0.5$ ; $t_p = 25 \mu s$ ; square-wave pulse current  non-repetitive peak forward current $t_p = 10 m s$ ; $t_{j(init)} = 25 ^{\circ}C$ ; sine-wave pulse; Fig. 3 $t_p = 8.3 m s$ ; $t_{j(init)} = 25 ^{\circ}C$ ; sine-wave pulse  Parameter Conditions  aracteristics  forward voltage $t_p = 30 A$ ; $t_p = 25 ^{\circ}C$ ; Fig. 5 $t_p = 30 A$ ; $t_p$	repetitive peak reverse voltage	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{ c c c c } \hline \text{repetitive peak reverse} \\ \hline \text{voltage} \\ \hline \text{average forward current} \\ \hline \text{average forward current} \\ \hline \text{average forward current} \\ \hline \text{repetitive peak forward current} \\ \hline \text{non-repetitive peak forward current} \\ \hline \text{non-repetitive peak forward current} \\ \hline \hline \text{t}_p = 10 \text{ ms; } T_{j(\text{init})} = 25 \text{ °C; sine-wave pulse;} \\ \hline \hline \text{Fig. 3} \\ \hline \text{t}_p = 8.3 \text{ ms; } T_{j(\text{init})} = 25 \text{ °C; sine-wave pulse;} \\ \hline \hline \text{Parameter} \\ \hline \hline \text{Conditions} \\ \hline \text{Notes} \\ \hline \text{Min} \\ \hline \text{Typ} \\ \hline \text{Max} \\ \hline \text{aracteristics} \\ \hline \text{forward voltage} \\ \hline \hline \text{I}_F = 30 \text{ A; } T_j = 25 \text{ °C; Fig. 5} \\ \hline \text{I}_F = 30 \text{ A; } T_j = 150 \text{ °C; Fig. 5} \\ \hline \text{I}_F = 30 \text{ A; } T_j = 150 \text{ °C; Fig. 5} \\ \hline \text{reverse recovery time} \\ \hline \hline \text{I}_F = 1 \text{ A; } V_R = 30 \text{ V; dI_F/dt} = 200 \text{ A/µs;} \\ \hline \end{array}  \begin{array}{c} - & 23 & - \\ \hline \end{array}$

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	А	anode	000	K — A 001aaa020
mb	n.c.	mounting base; isolated		001aaa020

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC31MX-650PS	TO220F-2L	BYC31MX-650PSQ	Tube	50	TO220Fd-2L	02-Aug-2022

# 7. Marking

### **Table 4. Marking codes**

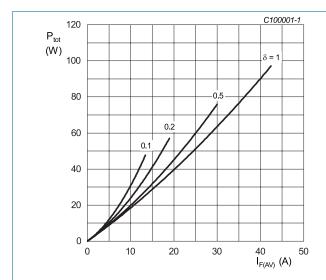
Type number	Marking codes
BYC31MX-650PS	BYC31MX 650PS

## 8. Limiting values

#### Table 5. Limiting values

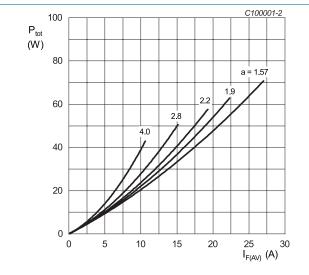
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			650	V
$V_{RWM}$	crest working reverse voltage			650	V
$V_R$	reverse voltage	DC		650	V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; Fig. 1; Fig. 2		30	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; square-wave pulse		60	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3		250	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		275	А
T <sub>stg</sub>	storage temperature			-65 to 175	°C
T <sub>j</sub>	junction temperature			-65 to 175	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 1.705 \text{ V}; \text{ R}_s = 0.0138 \text{ }\Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.705 V;  $R_s$  = 0.0138  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

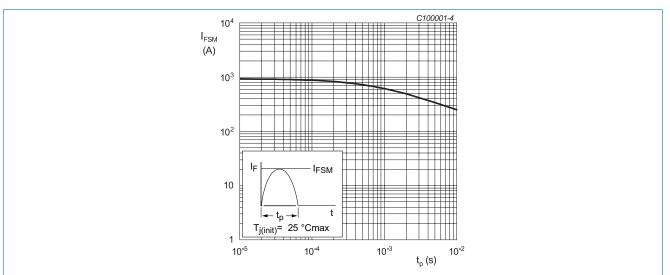
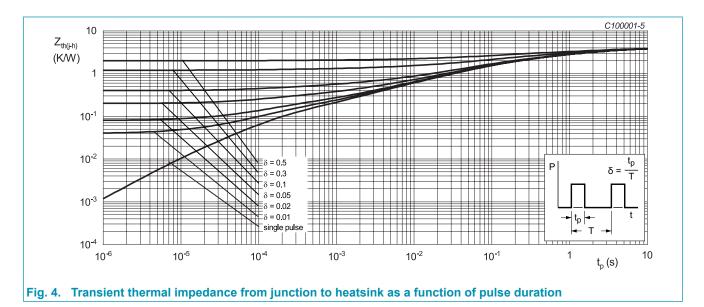


Fig. 3. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig. 4		-	-	4	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W



## 10. Isolation characteristics

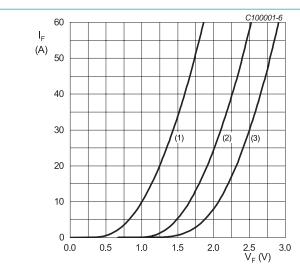
### **Table 7. Isolation characteristics**

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free		-	-	2500	V
C <sub>isol</sub>	isolation capacitance	f = 1 MHz; from cathode to external heatsink		-	10	-	pF

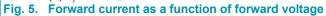
## 11. Characteristics

**Table 8. Characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
$V_{F}$	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	1.85	2.50	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.45	2.10	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.2	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	0.05	-	mA
Dynamic	characteristics						
Q <sub>r</sub> reverse charge	reverse charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$		-	200	-	nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 6$		-	650	-	nC
t <sub>rr</sub> reve	reverse recovery time	$I_F = 0.5 \text{ A}; I_{rr} = 0.25 \text{ A}; I_R = 1 \text{ A};$ $T_j = 25 \text{ °C}; Fig. 6$		-	36	-	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$		-	23	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$		-	72	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 6$		-	121	-	ns
I <sub>RM</sub> peak reverse recovery current		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$		-	5.4	-	А
		$I_F = 30 \text{ A}$ ; $V_R = 200 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 125 \text{ °C}$ ; Fig. 6		-	10.8	-	А
S <sub>factor</sub>	softness factor	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_J = 125 \text{ °C}; Fig. 6$		-	0.66	-	
E <sub>as</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C		16.8	-	-	mJ



 $V_o$  = 1.705 V;  $R_s$  = 0.0138 Ω (1)  $T_j$  = 150 °C; typical values (2)  $T_j$  = 150 °C; maximum values (3)  $T_j$  = 25 °C; maximum values



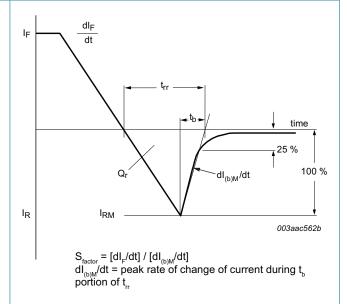
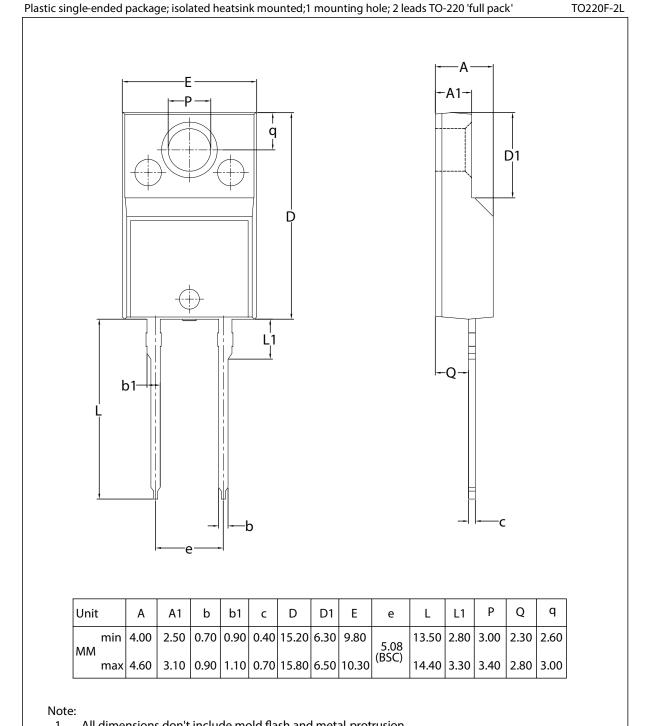


Fig. 6. Reverse recovery definitions; ramp recovery

# 12. Package outline



All dimensions don't include mold flash and metal protrusion.

## 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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